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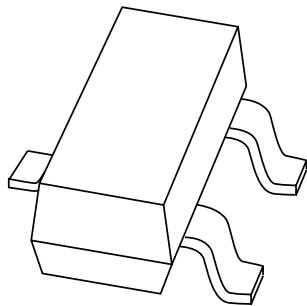
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If you have any questions related to the data sheet, please contact our nearest sales office via e-mail or telephone (details via **salesaddresses@nexperia.com**). Thank you for your cooperation and understanding,

Kind regards,

Team Nexperia

DATA SHEET



BSV52 NPN switching transistor

Product data sheet
Supersedes data of 1999 Apr 15

2004 Jan 14

NPN switching transistor

BSV52

FEATURES

- Low current (max. 100 mA)
- Low voltage (max. 12 V).

APPLICATIONS

- High speed saturated switching applications, especially in portable equipment.

DESCRIPTION

NPN switching transistor in a SOT23 plastic package.

MARKING

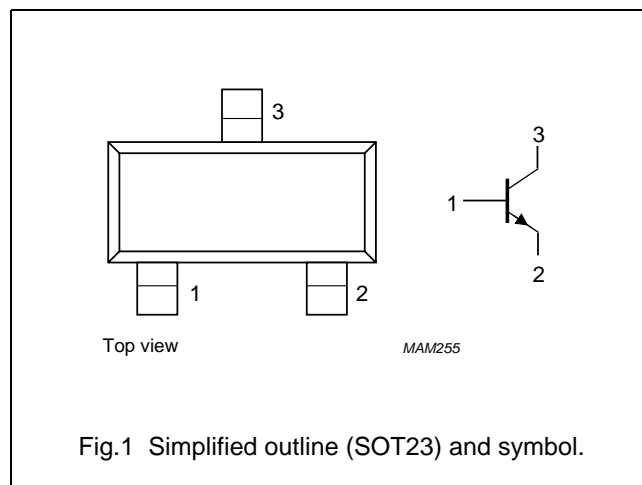
TYPE NUMBER	MARKING CODE ⁽¹⁾
BSV52	B2*

Note

1. * = p : Made in Hong Kong.
 * = t : Made in Malaysia.
 * = W: Made in China.

PINNING

PIN	DESCRIPTION
1	base
2	emitter
3	collector



ORDERING INFORMATION

TYPE NUMBER	PACKAGE		
	NAME	DESCRIPTION	VERSION
BSV52	–	plastic surface mounted package; 3 leads	SOT23

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter	–	20	V
V_{CEO}	collector-emitter voltage	open base	–	12	V
V_{EBO}	emitter-base voltage	open collector	–	5	V
I_C	collector current (DC)		–	100	mA
I_{CM}	peak collector current		–	200	mA
I_{BM}	peak base current		–	100	mA
P_{tot}	total power dissipation	$T_{amb} \leq 25\text{ °C}$	–	250	mW
T_{stg}	storage temperature		–65	+150	°C
T_j	junction temperature		–	150	°C
T_{amb}	operating ambient temperature		–65	+150	°C

NPN switching transistor

BSV52

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th(j-a)}$	thermal resistance from junction to ambient	note 1	500	K/W

Note

1. Transistor mounted on an FR4 printed-circuit board.

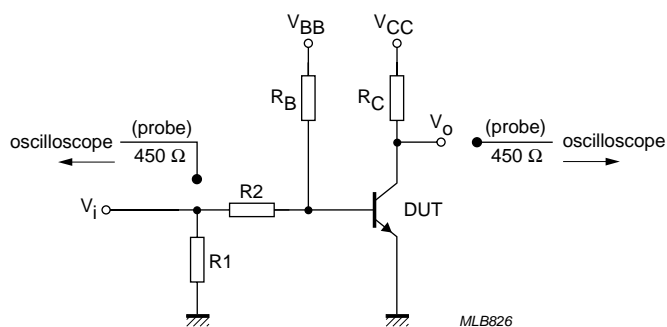
CHARACTERISTICS

$T_j = 25\text{ }^{\circ}\text{C}$ unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I_{CBO}	collector cut-off current	$I_E = 0; V_{CB} = 20\text{ V}$	—	—	400	nA
		$I_E = 0; V_{CB} = 20\text{ V}; T_j = 125\text{ }^{\circ}\text{C}$	—	—	30	μA
I_{EBO}	emitter cut-off current	$I_C = 0; V_{EB} = 4\text{ V}$	—	—	100	nA
h_{FE}	DC current gain	$V_{CE} = 1\text{ V}$				
		$I_C = 1\text{ mA}$	25	—	—	
		$I_C = 10\text{ mA}$	40	—	120	
		$I_C = 50\text{ mA}$	25	—	—	
V_{CEsat}	collector-emitter saturation voltage	$I_C = 10\text{ mA}; I_B = 300\text{ }\mu\text{A}$	—	—	300	mV
		$I_C = 10\text{ mA}; I_B = 1\text{ mA}$	—	—	250	mV
		$I_C = 50\text{ mA}; I_B = 5\text{ mA}$	—	—	400	mV
V_{BEsat}	base-emitter saturation voltage	$I_C = 10\text{ mA}; I_B = 1\text{ mA}$	700	—	850	mV
		$I_C = 50\text{ mA}; I_B = 5\text{ mA}$	—	—	1.2	V
C_c	collector capacitance	$I_E = i_e = 0; V_{CB} = 5\text{ V}; f = 1\text{ MHz}$	—	—	4	pF
C_e	emitter capacitance	$I_C = i_c = 0; V_{EB} = 1\text{ V}; f = 1\text{ MHz}$	—	—	4.5	pF
f_T	transition frequency	$I_C = 10\text{ mA}; V_{CE} = 10\text{ V}; f = 100\text{ MHz}$	400	500	—	MHz
Switching times (between 10% and 90% levels); (see Fig.2)						
t_{on}	turn-on time	$I_{Con} = 10\text{ mA}; I_{Bon} = 3\text{ mA};$ $I_{Boff} = -1.5\text{ mA}$	—	—	10	ns
t_d	delay time		—	—	4	ns
t_r	rise time		—	—	6	ns
t_{off}	turn-off time		—	—	20	ns
t_s	storage time		—	—	10	ns
t_f	fall time		—	—	10	ns

NPN switching transistor

BSV52



$V_i = 0.5 \text{ V to } 4.2 \text{ V}$; $T = 500 \text{ } \mu\text{s}$; $t_p = 10 \text{ } \mu\text{s}$; $t_r = t_s \leq 3 \text{ ns}$.

$R1 = 56 \text{ } \Omega$; $R2 = 1 \text{ k}\Omega$; $R_B = 1 \text{ k}\Omega$; $R_C = 270 \text{ } \Omega$.

$V_{BB} = 0.2 \text{ V}$; $V_{CC} = 2.7 \text{ V}$.

Oscilloscope: input impedance $Z_i = 50 \text{ } \Omega$.

Fig.2 Test circuit for switching times.

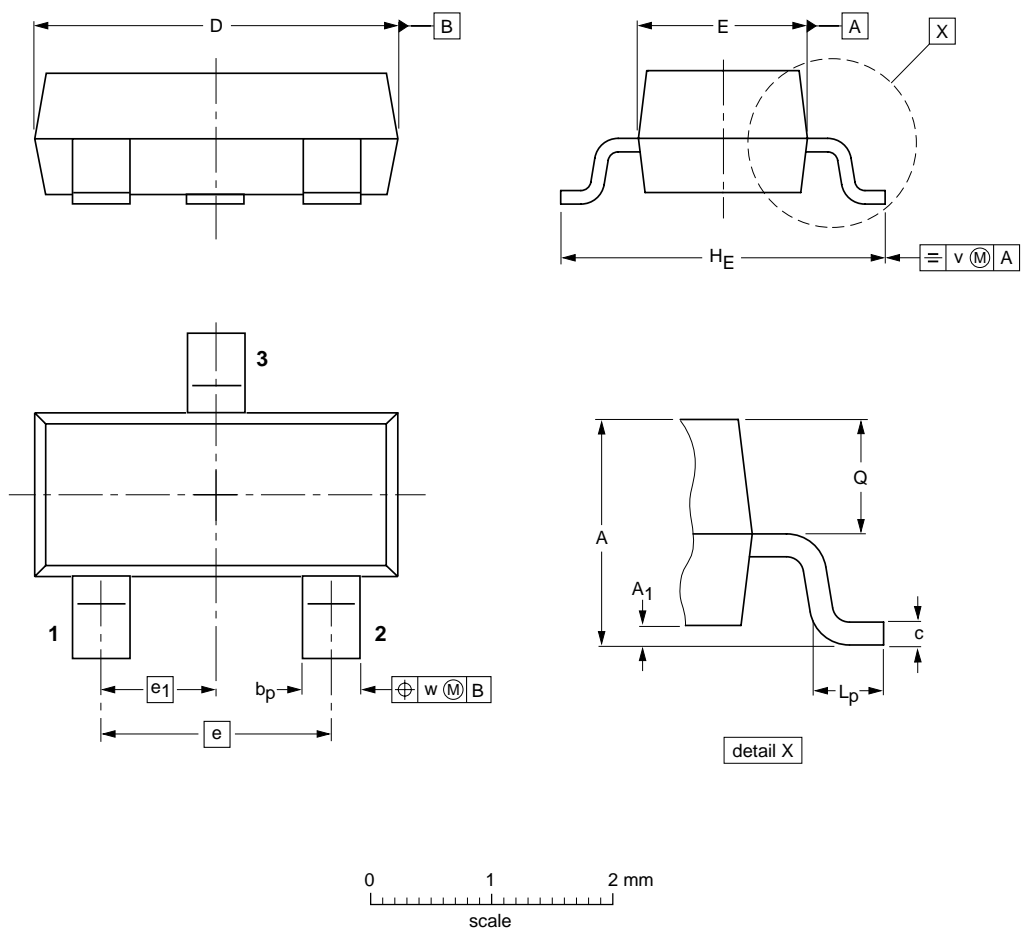
NPN switching transistor

BSV52

PACKAGE OUTLINE


Plastic surface-mounted package; 3 leads

SOT23



DIMENSIONS (mm are the original dimensions)

UNIT	A	A ₁ max.	b _p	c	D	E	e	e ₁	H _E	L _p	Q	v	w
mm	1.1 0.9	0.1	0.48 0.38	0.15 0.09	3.0 2.8	1.4 1.2	1.9	0.95	2.5 2.1	0.45 0.15	0.55 0.45	0.2	0.1

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT23		TO-236AB				04-11-04 06-03-16

NPN switching transistor

BSV52

DATA SHEET STATUS

DOCUMENT STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

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NXP Semiconductors

Customer notification

This data sheet was changed to reflect the new company name NXP Semiconductors, including new legal definitions and disclaimers. No changes were made to the technical content, except for package outline drawings which were updated to the latest version.

Contact information

For additional information please visit: **<http://www.nxp.com>**

For sales offices addresses send e-mail to: **salesaddresses@nxp.com**

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